

A10020896-1

## CLAIMS

1 1. (Original) A device comprising:  
2 a first layer;  
3 an etch stop layer positioned over the first layer;  
4 a second layer positioned over the etch stop layer;  
5 a first trench positioned through the second layer, etch stop layer, and a portion of  
6 the first layer.

1 2. (Original) A device, as defined in claim 1, wherein the etch stop layer is an  
2 oxide.

1 3. (Original) A device, as defined in claim 2, wherein the first layer is c-Si and  
2 the second layer is amorphous silicon.

1 4. (Original) A device, as defined in claim 2, wherein the first layer is c-Si and  
2 the second layer is epitaxial silicon.

1 5. (Original) A device, as defined in claim 2, wherein the first layer is low-k  
2 dielectric and the second layer is an amorphous Si.

1 6. (Original) A device, as defined in claim 5, wherein k is between 1 and 3.9.

1 7. (Original) A device, as defined in claim 1, further comprising an intermediary  
2 layer interposing the etch stop layer and first layer, the trench further extending through  
3 the intermediary layer.

1 8. (Original) A device, as defined in claim 1, further comprising a second trench  
2 positioned through the second layer, etch stop layer, and a portion of the first layer,  
3 wherein the second trench has a shallower depth than the first trench.

9 - 19. (Cancelled)

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